

FIG. 1

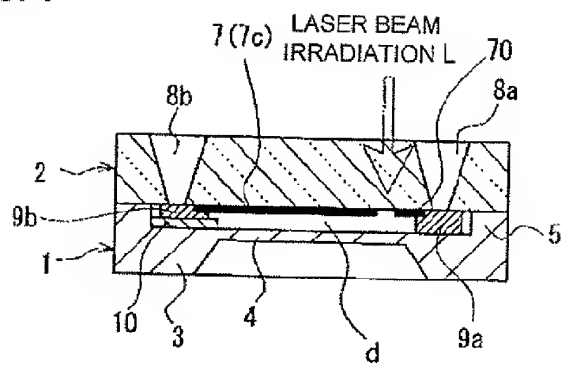


FIG. 2

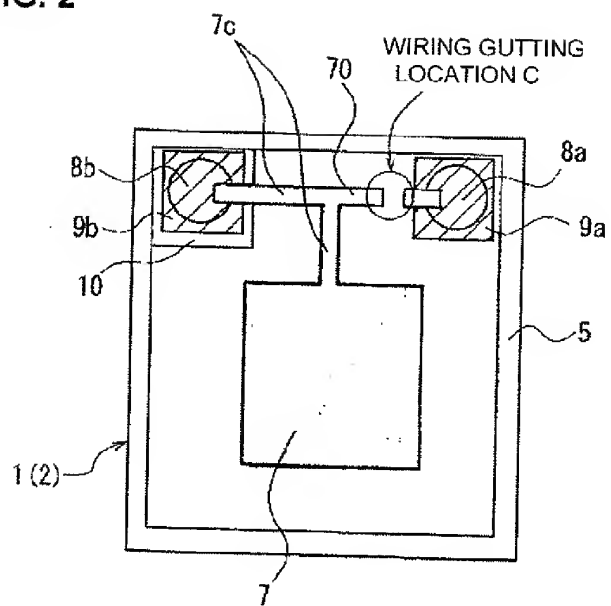


FIG. 3

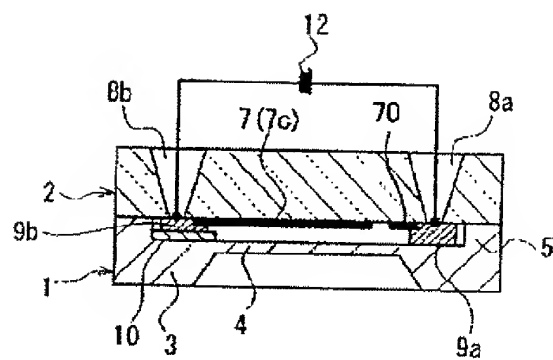


FIG. 4

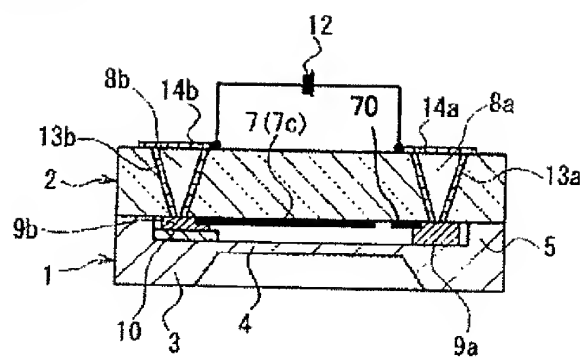


FIG. 5

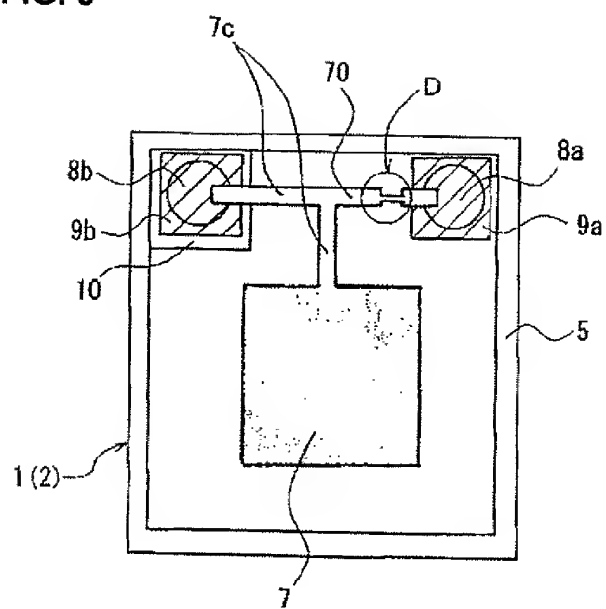


FIG. 6

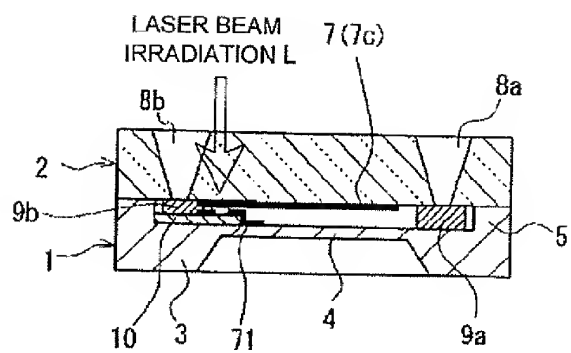


FIG. 7

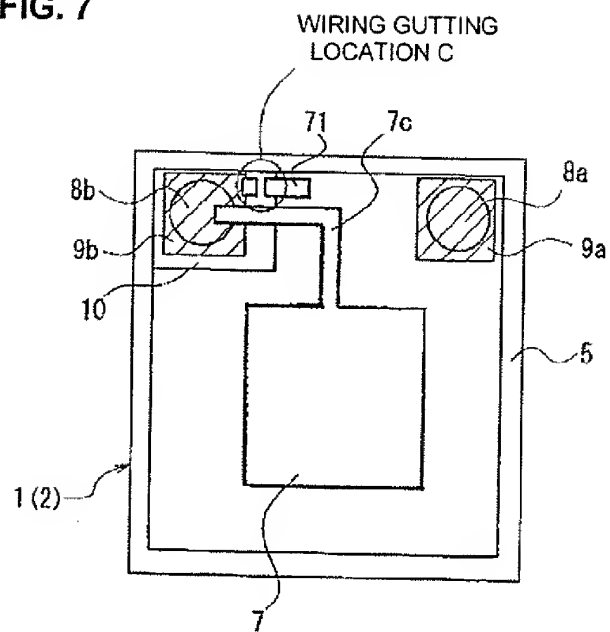


FIG. 8

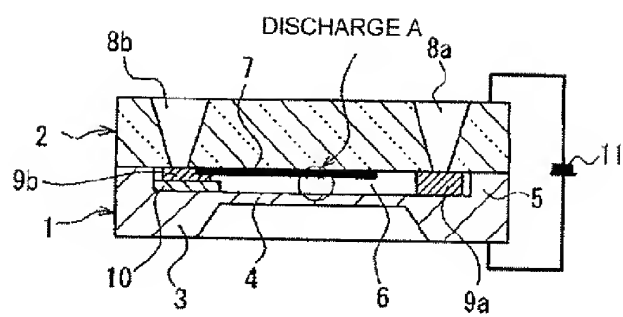


FIG. 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 1, a gate 2, a gate oxide film 3, a gate electrode 4, a gate insulating film 5, a gate contact 6, a gate pad 7 (7c), a gate terminal 8a, a gate terminal 8b, a gate terminal 9a, a gate terminal 9b, and a gate terminal 10. A gate terminal 11 is also shown.

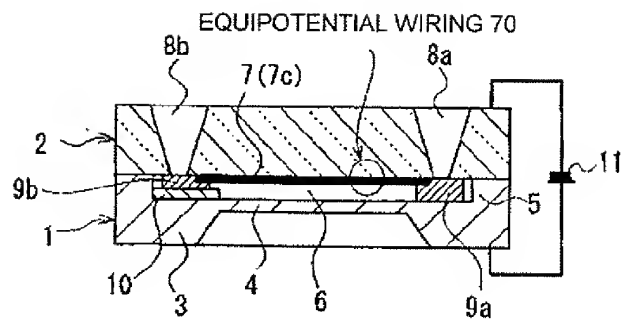


FIG. 10

